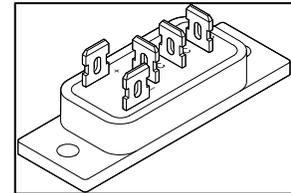


TECHNICAL DATA  
DATA SHEET 1176, REV -

**THREE PHASE FULL WAVE  
BRIDGE RECTIFIER ASSEMBLY**



DESCRIPTION: AN 800/1000 VOLT, 25 AMP, 5000 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

**MAXIMUM RATINGS**

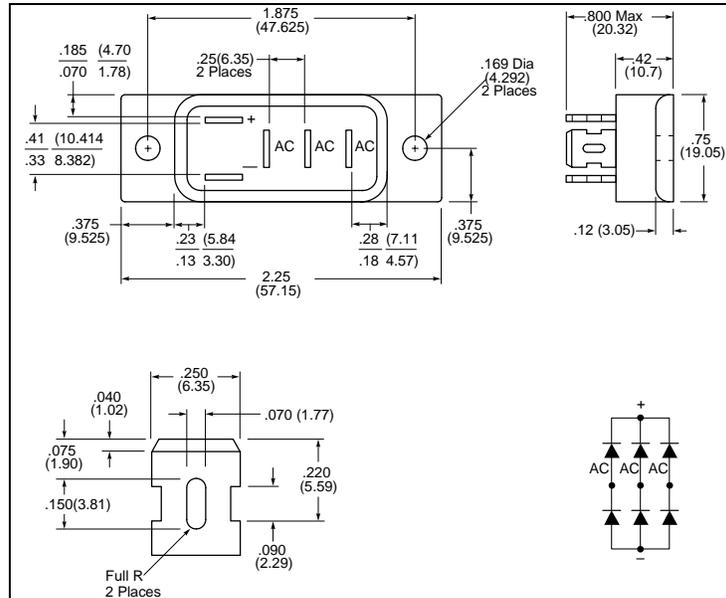
All ratings are at  $T_A = 25^\circ\text{C}$  unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV) S25A380 S25A3100	-	-	-	800 1000	Vdc
Average DC Output Current ( $T_C = \text{Case Temp}$ ) ( $I_o$ )	$T_C = 55^\circ\text{C}$ $T_C = 100^\circ\text{C}$ $T_C = 125^\circ\text{C}$	-	-	25 18.5 12.5	Amps
Average DC Output Current Ambient Temp. (no heat sink) ( $I_o$ )	$T_A = 25^\circ\text{C}$ $T_A = 55^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	6.0 5.0 3.0	Amps
Peak Single Cycle Surge Current ( $I_{FSM}$ )	$t_p = 8.3$ ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	150	Amps(pk)
Thermal Resistance ( $\theta_{JL}$ )	-	-	-	1.5	$^\circ\text{C/W}$
Operating and Storage Temp. ( $T_{op}$ & $T_{stg}$ )	-	-55	-	+150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS**

CHARACTERISTICS	CONDITIONS	MIN	TYP	MAX	UNIT
Maximum Forward Voltage ( $V_f$ )	$I_f = 9\text{A}$ (300 $\mu\text{sec}$ pulse, duty cycle < 2%)	-	-	1.4	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	5.0 100	$\mu\text{Amps}$
Reverse Recovery Time ( $t_{rr}$ )	$I_f = 0.5\text{A}$ , $I_r = 1.0\text{A}$ , $I_{rr} = 0.25\text{A}$	-	-	5000	nsec

**MECHANICAL DIMENSIONS: In Inches / mm**



**FIG. 404**

Note: Case finish - Black Anodized

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